

SILICON EPITAXIAL PLANAR DIODE

Band Switching Diode

Features

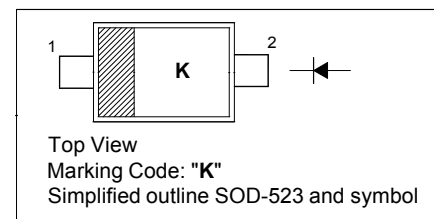
- Extremely small surface mounting type
- High reliability

Applications

- High frequency switching

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | Cathode |
| 2 | Anode |



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|---------------------------|-----------|---------------|------------------|
| Reverse Voltage | V_R | 35 | V |
| Forward Current | I_F | 100 | mA |
| Junction Temperature | T_J | 125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | - 55 to + 125 | $^\circ\text{C}$ |

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Max. | Unit |
|---|--------|------|----------|
| Forward Voltage at $I_F = 10\text{ mA}$ | V_F | 1 | V |
| Reverse Current at $V_R = 25\text{ V}$ | I_R | 10 | nA |
| Capacitance Between Terminals at $V_R = 6\text{ V}$, $f = 1\text{ MHz}$ | C_T | 1.2 | pF |
| Forward Operating Resistance at $I_F = 2\text{ mA}$, $f = 100\text{ MHz}$ | R_F | 0.7 | Ω |

1SS270

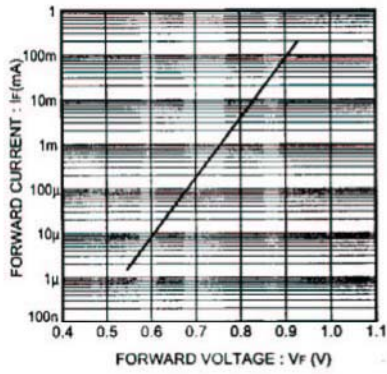


Fig. 1 Forward characteristics

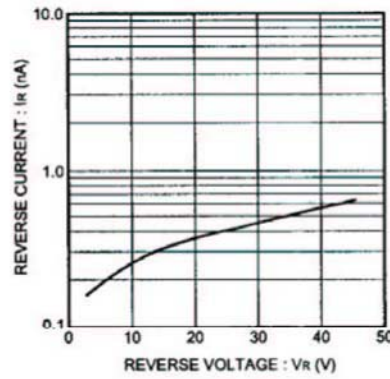


Fig. 2 Reverse characteristics

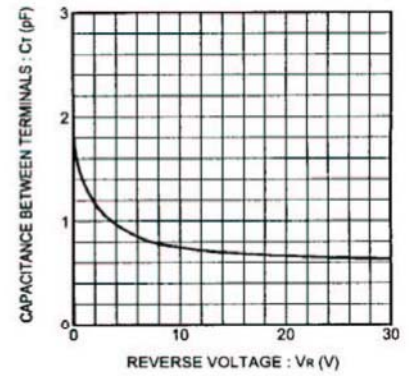


Fig. 3 Capacitance between terminals characteristics

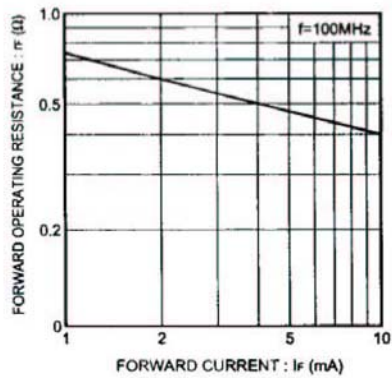


Fig. 4 Forward operating resistance characteristics